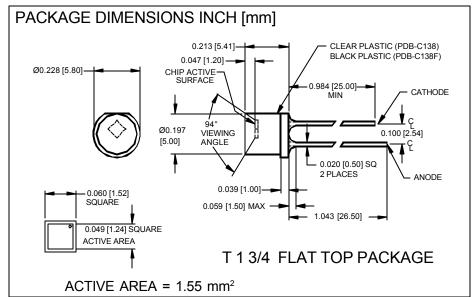
# **PHOTONIC** Silicon Photodiode, Blue Enhanced Photoconductive **DETECTORS INC.** Type PDB-C136, with daylight filter Type PDB-C136F





### **FEATURES**

- Large active area
- Photoconductive
- Low cost
- High speed

**DESCRIPTION:** The **PDB-C136** detector is a 1.55 mm<sup>2</sup> planar PIN photodiode packaged in a T 1 3/4, flat top, water clear plastic housing. Designed for high speed, low capacitance, photoconductive applications. The **PDB-C136F** includes a daylight filter.

## **APPLICATIONS**

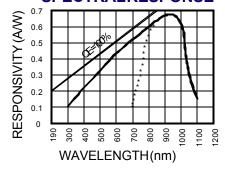
- Smoke detectors
- Light pen detectors
- Fiber optics
- Bar code detectors

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{\mathtt{BR}}$	Reverse Voltage		100	V
$T_{STG}$	Storage Temperature	-40	+100	∞
T <sub>O</sub>	Operating Temperature Range	-40	+80	∞
T <sub>s</sub>	Soldering Temperature*		+260	∘C
١ <sub>L</sub>	Light Current		500	mA

<sup>\*1/16</sup> inch from case for 3 secs max

## **SPECTRALRESPONSE**



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l <sub>sc</sub>	Short Circuit Current	H = 100 fc, 2850 K	20	27		μΑ
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 10 V		2	30	nA
R <sub>sH</sub>	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	.5	2		GΩ
TCR <sub>SH</sub>	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V*		6	10	рF
λrange	Spectral Application Range	(without daylight filter)**	400		1100	nm
λр	Spectral Response - Peak			950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	50	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		1.8x10 <sup>-13</sup>		W/ √ Hz
tr	Response Time	RL = $1 \text{ K}\Omega \text{ V}_{p} = 50 \text{ V}$		10		nS